

**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

Docket Number (Optional)  
**CS03-048**

Application Number

Applicant(s)  
**Yisuo Li**

Filing Date

Group Art Unit

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WLL		US 5,970,300		(Buynoski)			
WLL		US 6,566,204		( Wang, et al.)			
WLL		US 6,599,804		(Bulucea, et al.			
WLL		US 4,728,617		Woo, et al			
WLL		US 5,729,045		Buynoski			

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)


EXAMINER

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JUL 07 2004

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jan 30,2004

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INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Masahi Shima, "<100> Strained-SiGe- channel p-MOSFET with enhanced hole mobility and lower parasitic Resistance", Fujitsu Sci. Tech. J.,39,1, p. 78-83 (June 2003).

Oldiges, et al., " Molecular Dynamics Simulations of LATID implants into Silicon", found on Website <http://beam.helsinki.fi/~knordlun/pub/sispad97.pdf> ~ 3-1-2004 see <http://www.acclab.helsinki.fi/~knordlun/pub/>

Brand et al., Intel's 0.25 micron, 2.0V logic process technology, Intel.Technology Journal Q3,98, pp. 1-4.

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